10-0B066PA020SB-M995F09
datasheet

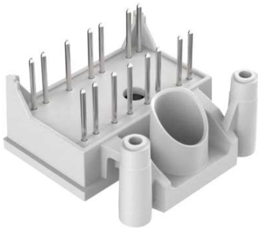
Vincotech

***flow*PACK 0 B** — **600 V / 20 A**

Features

- IGBT3 (600 V) technology
- Open emitter topology
- New ultra-compact housing
- Single-screw heat sink mounting

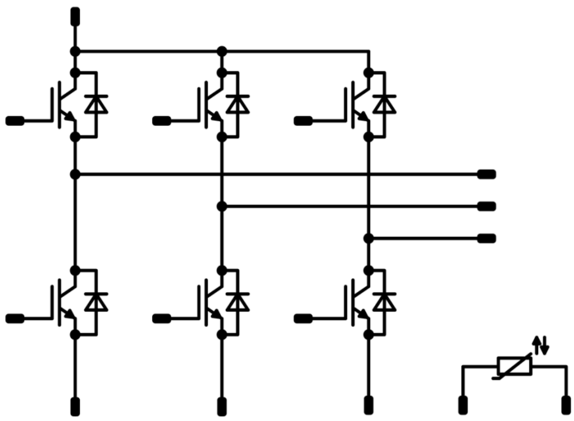
flow 0 B 17mm housing



Target applications

- Dedicated design for motor drive

Schematic



Types

- 10-0B066PA020SB-M995F09

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Condition	Value	Unit
Inverter Switch				
Collector-emitter voltage	V_{CES}		600	V
Collector current	I_C	$T_j = T_{jmax}$ T_s = 80 °C	21	A
Repetitive peak collector current	I_{CRM}	t_p limited by T_{jmax}	60	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	41	W
Gate-emitter voltage	V_{GES}		±20	V
Short circuit ratings	t_{SC} V_{CC}	$T_j \leq 150$°C V_{GE} = 15V	6 360	µs V
Maximum Junction Temperature	T_{jmax}		175	°C

Parameter	Symbol	Condition		Value	Unit
Inverter Diode					
Peak Repetitive Reverse Voltage	V_{RRM}			600	V
Continuous (direct) forward current	I_F	$T_j = T_{jmax}$	T_s = 80 °C	22	A
Repetitive peak forward current	I_{FRM}			40	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$	T_s = 80 °C	34	W
Maximum Junction Temperature	T_{jmax}			175	°C

Module Properties

Thermal Properties

Parameter	Symbol	Condition		Value	Unit
Storage temperature	T_{stg}			-40…+125	°C
Operation temperature under switching condition	T_{jop}			-40…+(T_{jmax} - 25)	°C

Isolation Properties

Parameter	Symbol	Condition		Value	Unit
Isolation voltage	V_{isol}	DC Voltage	t_p = 2s	4000	V
Creepage distance				min. 12,7	mm
Clearance				min. 12,7	mm
Comparative Tracking Index	CTI			> 200	

Characteristic Values

Parameter	Symbol	Conditions	V_{GE} [V] / V_{GS} [V]	V_{CE} [V] / V_{GS} [V] / V_r [V]	I_C [A] / I_D [A] / I_F [A]	T_j [°C]	Min	Typ	Max	Unit
Inverter Switch										
Static										
Gate-emitter threshold voltage	$V_{GE(th)}$	$V_{GE} = V_{CE}$			0,00029	25	5	5,8	6,5	V
Collector-emitter saturation voltage	V_{CEsat}		15		20	25 150	1,1	1,52 1,84	1,9	V
Collector-emitter cut-off current	I_{CES}		0	600		25			1,1	µA
Gate-emitter leakage current	I_{GES}		20	0		25			300	nA
Internal gate resistance	r_g							none		Ω
Input capacitance	C_{ies}	f = 1 MHz	0	25		25		1100		pF
Output capacitance	C_{oes}							71		
Reverse transfer capacitance	C_{res}							32		
Gate charge	Q_g		15	480	20	25		120		nC
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	Thermal grease thickness ≤ 50 µm λ = 1 W/mK						2,30		K/W
IGBT Switching										
Turn-on delay time	$t_{d(on)}$	R_{goff} = 16 Ω R_{gon} = 16 Ω	±15	300	20	25 150		71 70		ns
Rise time	t_r					25 150		11 16		
Turn-off delay time	$t_{d(off)}$					25 150		122 143		
Fall time	t_f					25 150		91 111		
Turn-on energy (per pulse)	E_{on}	Q_{rFWD} = 0,8 µC Q_{rFWD} = 1,7 µC				25 150		0,259 0,380		mWs
Turn-off energy (per pulse)	E_{off}					25 150		0,448 0,613		

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Parameter	Symbol	Conditions					Value			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{GS} [V] V_r [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Inverter Diode										
Static										
Forward voltage	V_F				20	25 125		1,70 1,58	1,95	V
Reverse leakage current	I_r			600		25 150			27	µA
Thermal										
Thermal resistance junction to sink	$R_{th(j-s)}$	Thermal grease thickness ≤ 50 µm λ = 1 W/mK						2,80		K/W
FWD Switching										
Peak recovery current	I_{RRM}	di/dt = 2072 A/µs di/dt = 1922 A/µs	±15	300	20	25 150		22 26		A
Reverse recovery time	t_{rr}					25 150		125 204		ns
Recovered charge	Q_r					25 150		0,809 1,713		µC
Reverse recovered energy	E_{rec}					25 150		0,171 0,373		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 150		2050 741		A/µs
Thermistor										
Rated resistance	R					25		21,5		kΩ
Deviation of R100	$\Delta_{R/R}$	R100=1486 Ω				100	-4,5		+4,5	%
Power dissipation	P					25		210		mW
Power dissipation constant						25		3,5		mW/K
B-value	$B_{(25/50)}$					25		3884		K
B-value	$B_{(25/100)}$					25		3964		K
Vincotech NTC Reference									F	

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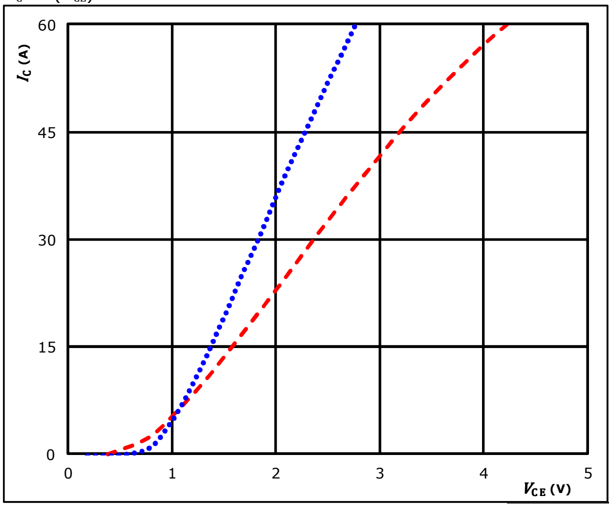
Inverter Switch Characteristics

Typical output characteristics **IGBT**

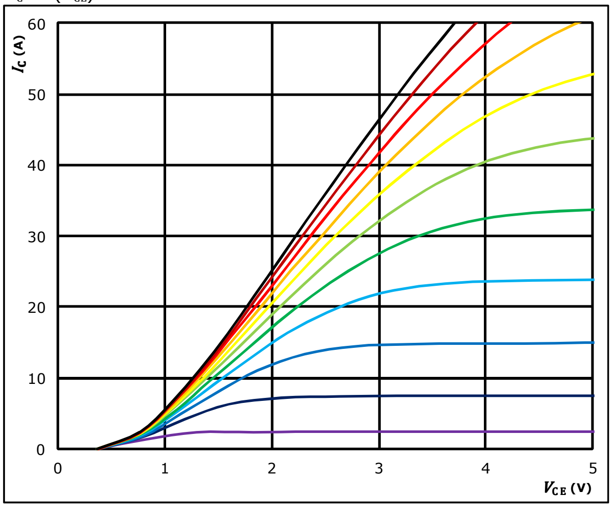
$I_C = f(V_{CE})$



t_p = 250 µs; V_{GE} = 15 V; T_j: 25 °C (dotted), 150 °C (dashed)

Typical output characteristics **IGBT**

$I_C = f(V_{CE})$



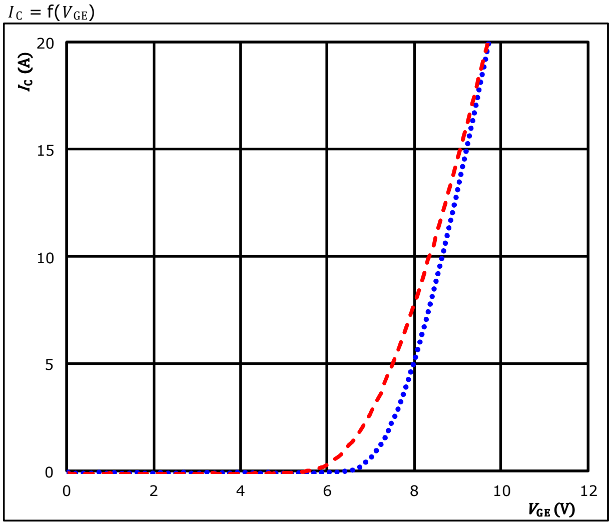
t_p = 250 µs

T_j = 150 °C

V_{GE} from 7 V to 17 V in steps of 1 V

Typical transfer characteristics **IGBT**

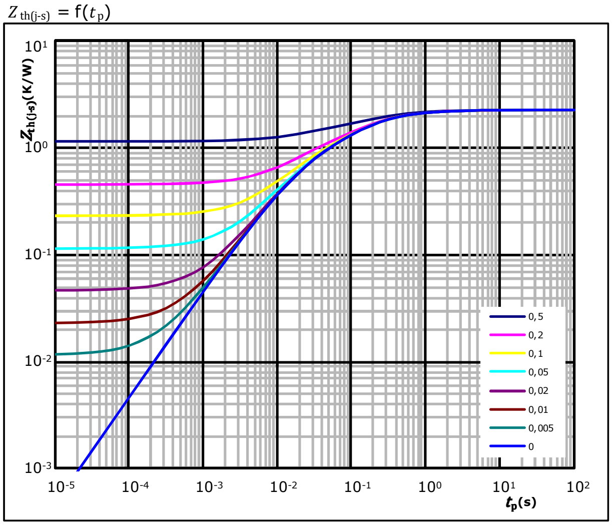
$I_C = f(V_{GE})$



t_p = 100 µs; V_{CE} = 10 V; T_j: 25 °C (dotted), 150 °C (dashed)

Transient Thermal Impedance as function of Pulse duration **IGBT**

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,30 K/W

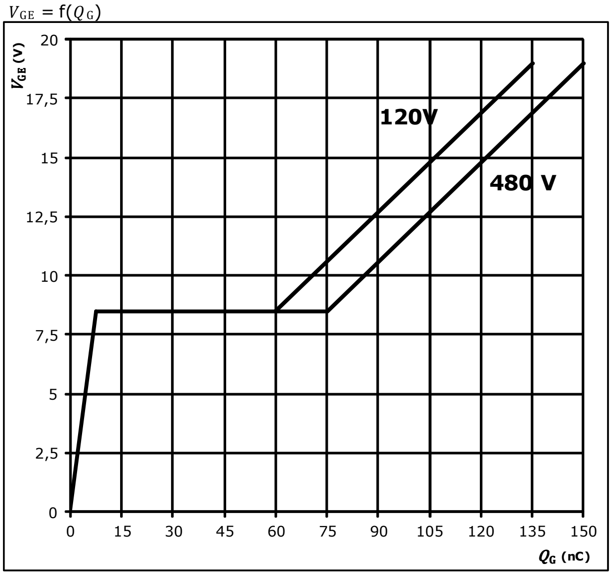
IGBT thermal model values

R (K/W)	τ (s)
8,31E-02	4,36E+00
2,54E-01	7,20E-01
9,17E-01	1,88E-01
6,06E-01	5,84E-02
4,40E-01	1,40E-02

Inverter Switch Characteristics

Gate voltage vs Gate charge **IGBT**

$V_{GE} = f(Q_G)$

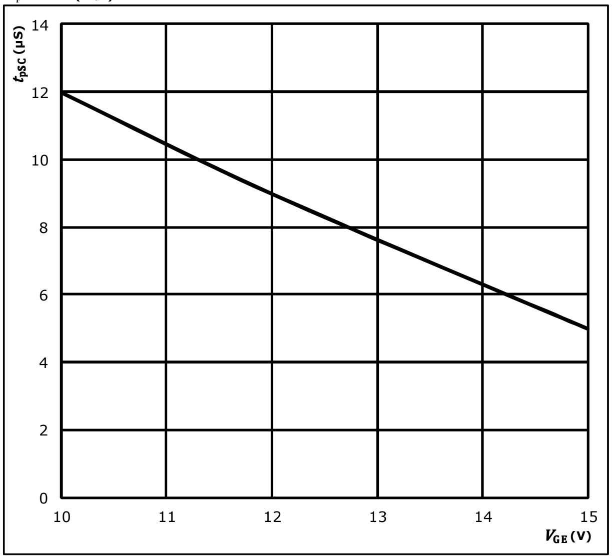


At

I_C=	20	A

Short circuit duration as a function of V_{GE} **IGBT**

$t_{pSC} = f(V_{GE})$

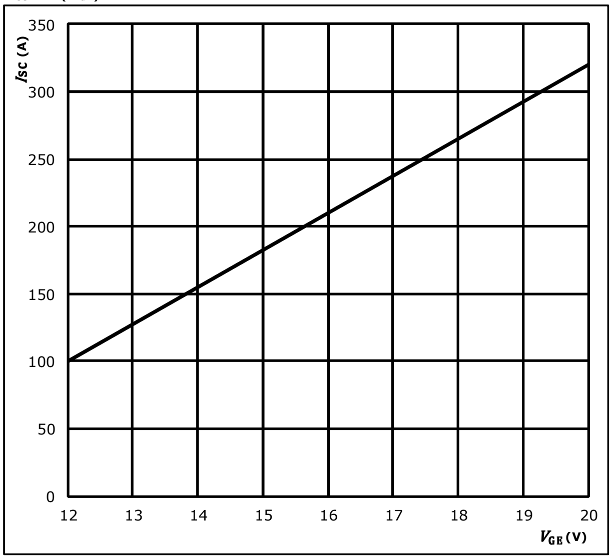


At

V_{CE} =	600	V
T_j ≤	175	ºC

Typical short circuit current as a function of V_{GE} **IGBT**

$I_{SC} = f(V_{GE})$



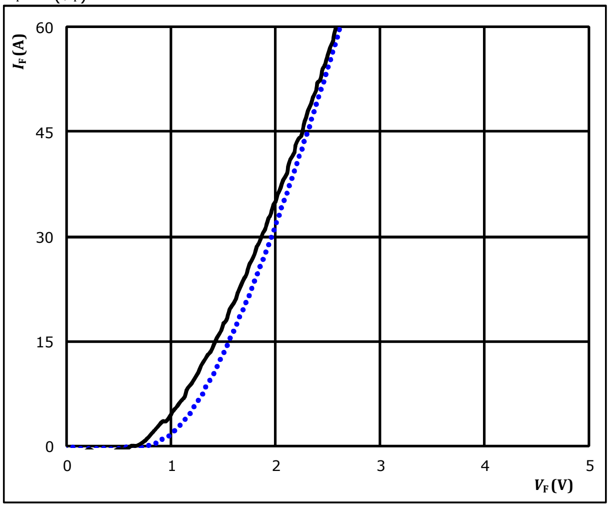
At

V_{CE} ≤	600	V
T_j ≤	175	ºC

Inverter Diode Characteristics

Typical forward characteristics **FWD**

$I_F = f(V_F)$

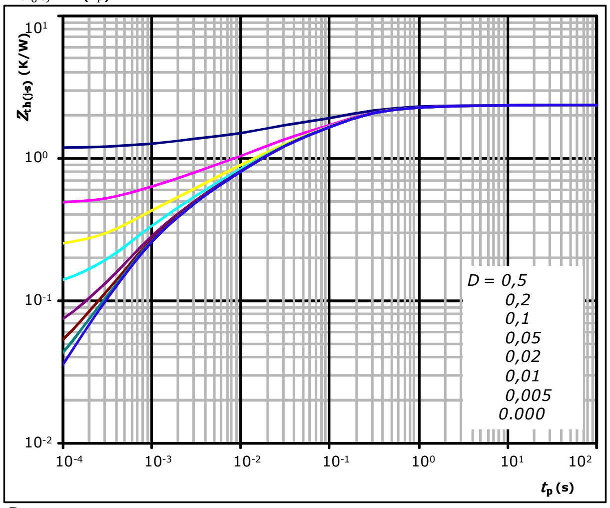


t_p = 250 μs

T_j: 25 °C (dotted), 125 °C (solid)

Transient thermal impedance as a function of pulse width **FWD**

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 2,37 K/W

FWD thermal model values

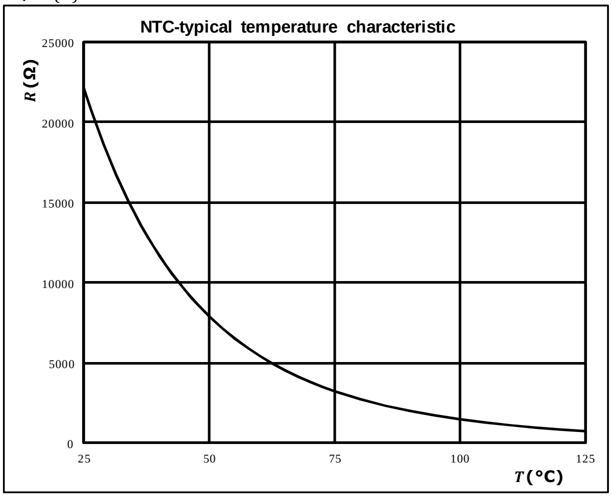
R (K/W)	τ (s)
4,62E-02	8,95E+00
1,39E-01	1,10E+00
6,93E-01	1,96E-01
5,75E-01	6,44E-02
6,19E-01	9,95E-03
2,95E-01	1,01E-03

Thermistor

Thermistor typical temperature characteristic

Typical NTC characteristic
as a function of temperature

$R_T = f(T)$

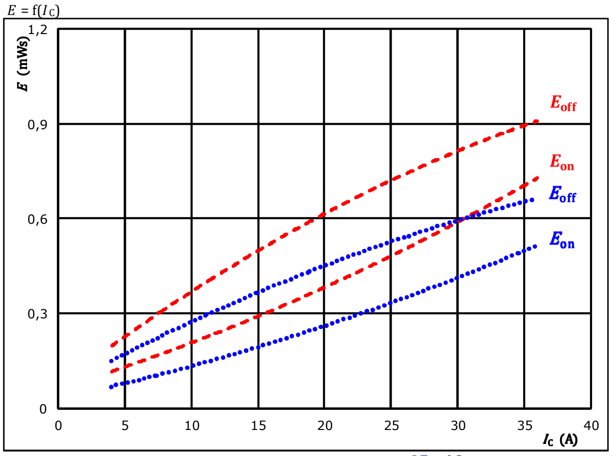


Inverter Switching Characteristics

figure 1. **IGBT**

Typical switching energy losses as a function of collector current

$E = f(I_C)$



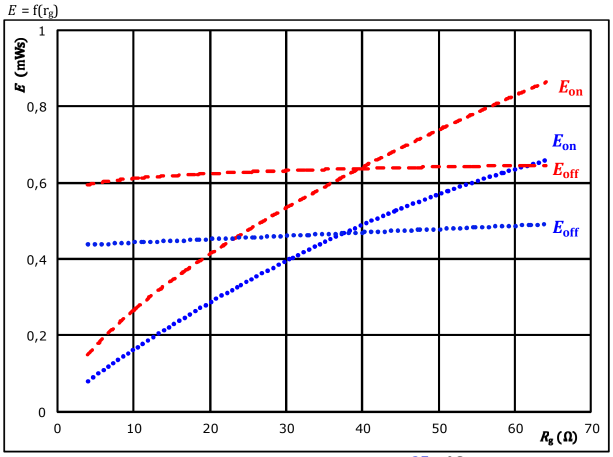
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C	············
V_{GE} =	±15	V		150 °C	– – – –
R_{gon} =	16	Ω			
R_{goff} =	16	Ω			

figure 2. **IGBT**

Typical switching energy losses as a function of gate resistor

$E = f(r_g)$



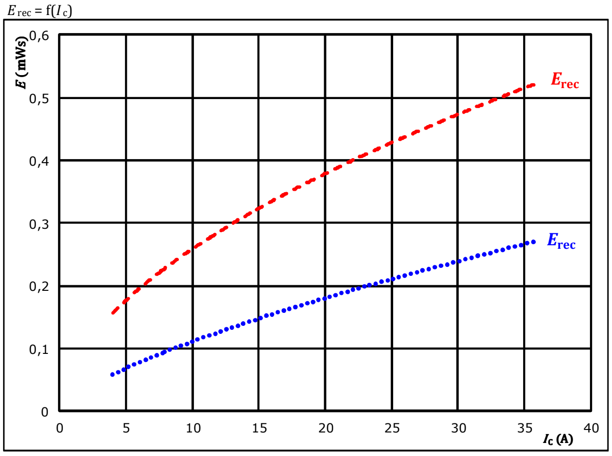
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C	············
V_{GE} =	±15	V		150 °C	– – – –
I_C =	20	A			

figure 3. **FWD**

Typical reverse recovered energy loss as a function of collector current

$E_{rec} = f(I_C)$



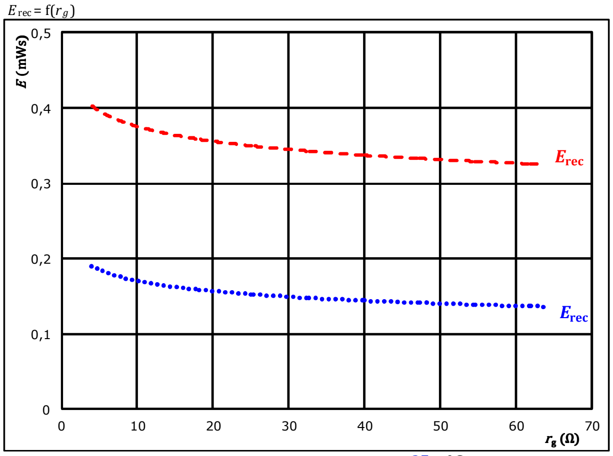
With an inductive load at

V_{CE} =	300	V	T_j:	25 °C	············
V_{GE} =	±15	V		150 °C	– – – –
R_{gon} =	16	Ω			

figure 4. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(r_g)$



With an inductive load at

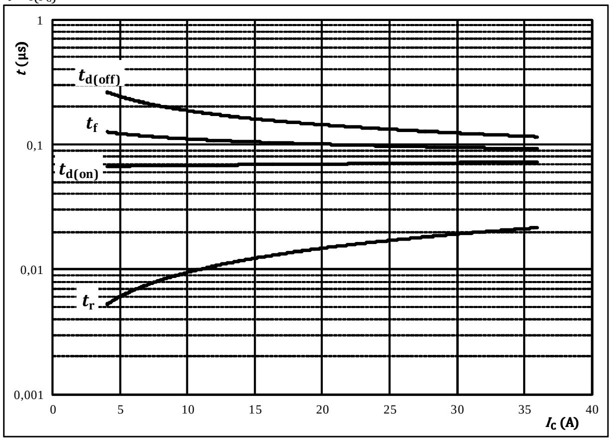
V_{CE} =	300	V	T_j:	25 °C	············
V_{GE} =	±15	V		150 °C	– – – –
I_C =	20	A			

Inverter Switching Characteristics

figure 5.	**IGBT**

Typical switching times as a function of collector current

$t = f(I_C)$



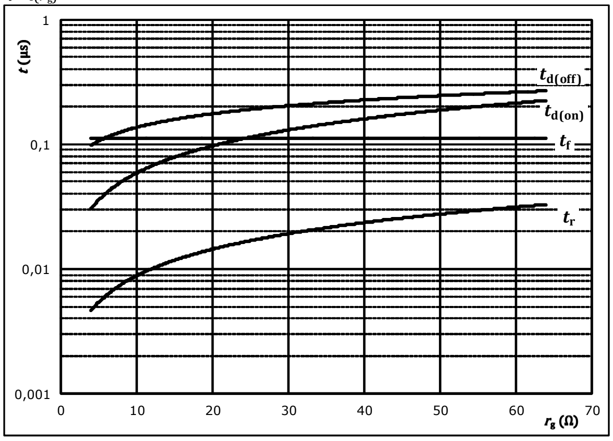
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
R_{gon} =	16	Ω
R_{goff} =	16	Ω

figure 6.	**IGBT**

Typical switching times as a function of gate resistor

$t = f(r_g)$



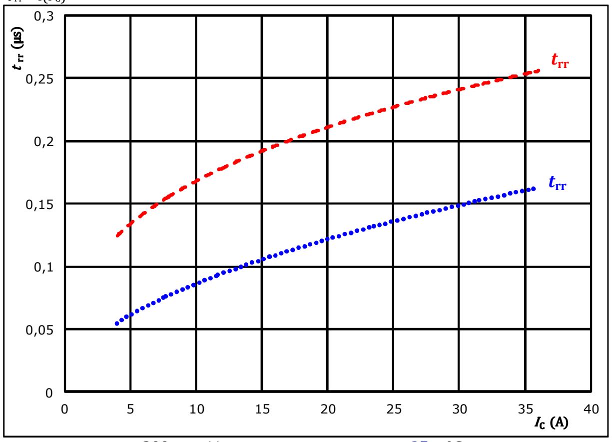
With an inductive load at

T_j =	150	°C
V_{CE} =	300	V
V_{GE} =	±15	V
I_C =	20	A

figure 7.	**FWD**

Typical reverse recovery time as a function of collector current

$t_{rr} = f(I_C)$

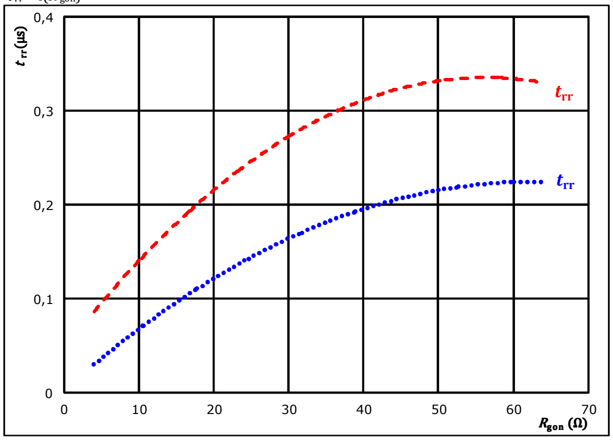


At	V_{CE}=	300	V		25	°C
	V_{GE} =	±15	V	T_j:	150	°C
	R_{gon} =	16	Ω			

figure 8.	**FWD**

Typical reverse recovery time as a function of IGBT turn on gate resistor

$t_{rr} = f(R_{gon})$



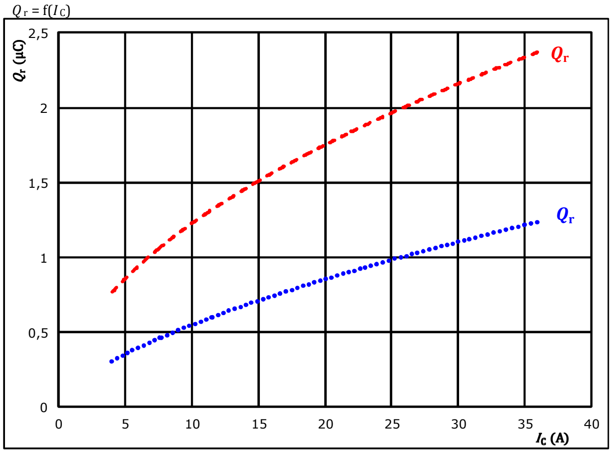
At	V_{CE} =	300	V		25	°C
	V_{GE} =	±15	V	T_j:	150	°C
	I_C =	20	A			

Inverter Switching Characteristics

figure 9. **FWD**

Typical recovered charge as a function of collector current

$Q_r = f(I_C)$

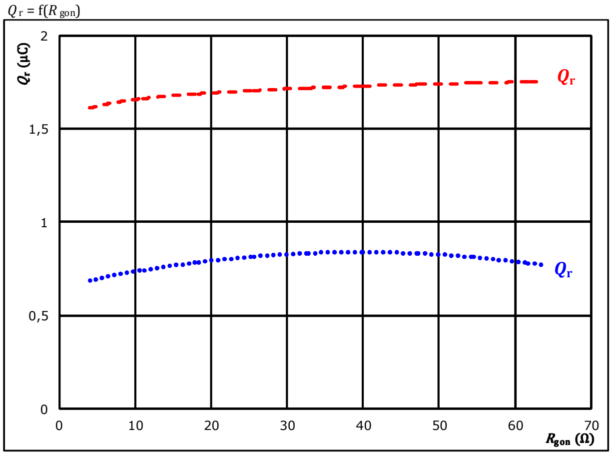


At					
V_{CE} =	300	V		25	°C
V_{GE} =	±15	V	T_j:	150	°C
R_{gon} =	16	Ω			

figure 10. **FWD**

Typical recoved charge as a function of IGBT turn on gate resistor

$Q_r = f(R_{gon})$

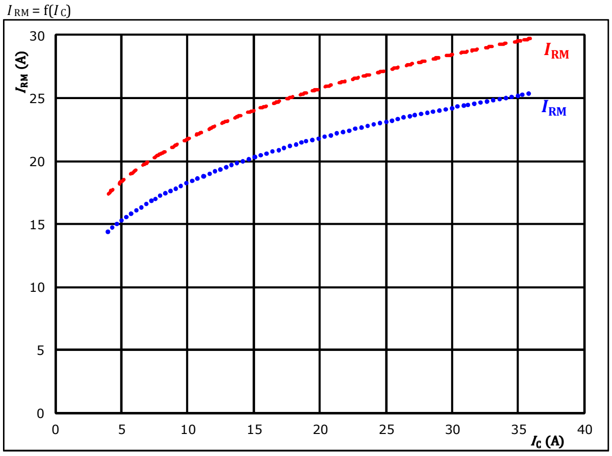


At					
V_{CE} =	300	V		25	°C
V_{GE} =	±15	V	T_j:	150	°C
I_C =	20	A			

figure 11. **FWD**

Typical peak reverse recovery current current as a function of collector current

$I_{RM} = f(I_C)$

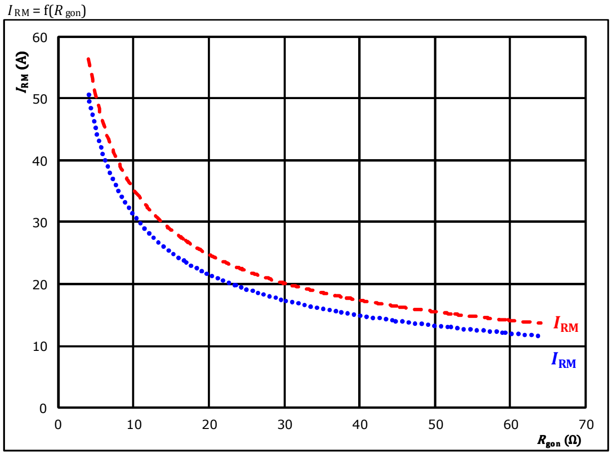


At					
V_{CE} =	300	V		25	°C
V_{GE} =	±15	V	T_j:	150	°C
R_{gon} =	16	Ω			

figure 12. **FWD**

Typical peak reverse recovery current as a function of IGBT turn on gate resistor

$I_{RM} = f(R_{gon})$



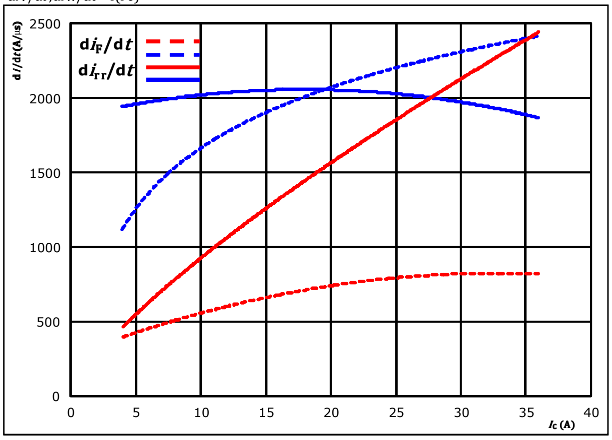
At					
V_{CE} =	300	V		25	°C
V_{GE} =	±15	V	T_j:	150	°C
I_C =	20	A			

Inverter Switching Characteristics

figure 13. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of collector current

$di_F/dt, di_{rr}/dt = f(I_C)$



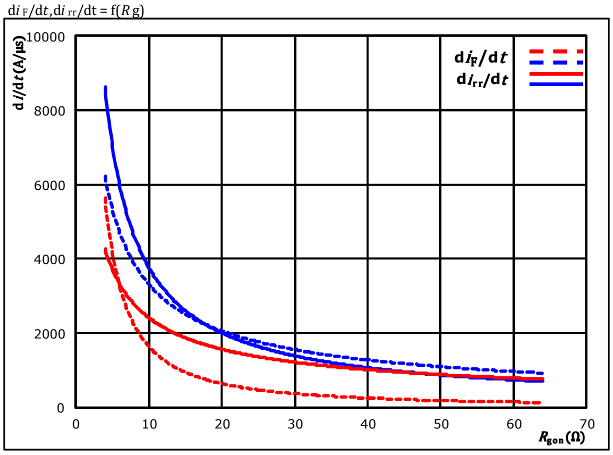
At

V_{CE} =	300	V	T_j:	25	°C
V_{GE} =	±15	V		150	°C
R_{gon} =	16	Ω			

figure 14. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of IGBT turn on gate resistor

$di_F/dt, di_{rr}/dt = f(R_g)$



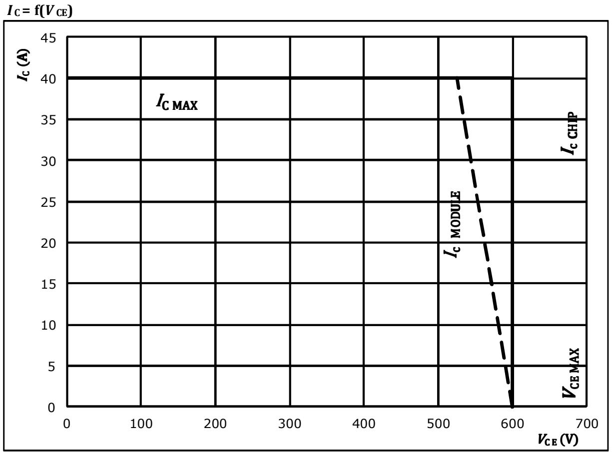
At

V_{CE} =	300	V	T_j:	25	°C
V_{GE} =	±15	V		150	°C
I_C =	20	A			

figure 15. **IGBT**

Reverse bias safe operating area

$I_C = f(V_{CE})$



At

T_j =	175	°C
R_{gon} =	16	Ω
R_{goff} =	16	Ω

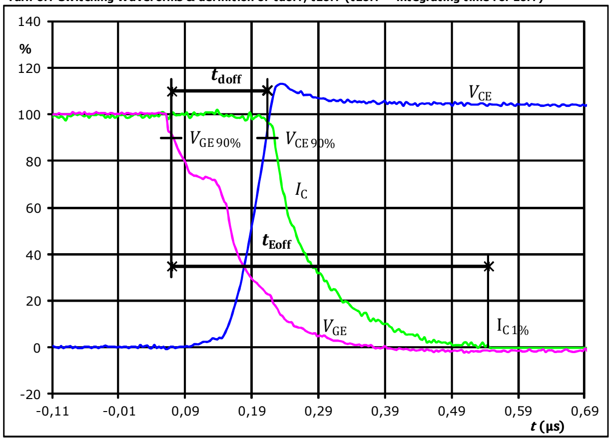
Inverter Switching Definitions

General conditions

T_j	=	150 °C
R_{gon}	=	16 Ω
R_{goff}	=	16 Ω

figure 1. **IGBT**

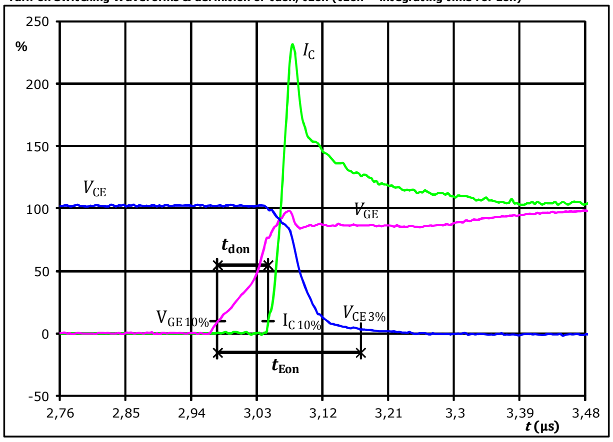
Turn-off Switching Waveforms & definition of tdoff, tEoff (tEoff = integrating time for Eoff)



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	300	V
$I_C(100\%)$ =	20	A
t_{doff} =	0,143	µs
t_{Eoff} =	0,476	µs

figure 2. **IGBT**

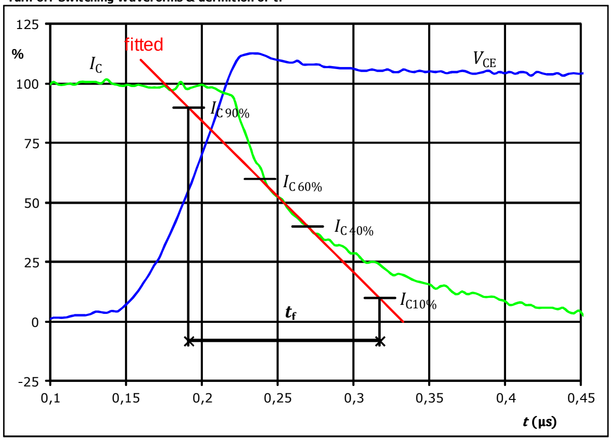
Turn-on Switching Waveforms & definition of tdon, tEon (tEon = integrating time for Eon)



$V_{GE}(0\%)$ =	-15	V
$V_{GE}(100\%)$ =	15	V
$V_C(100\%)$ =	300	V
$I_C(100\%)$ =	20	A
t_{don} =	0,070	µs
t_{Eon} =	0,196	µs

figure 3. **IGBT**

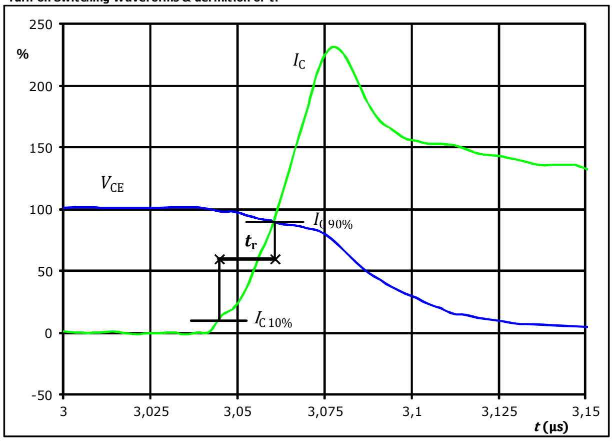
Turn-off Switching Waveforms & definition of tf



$V_C(100\%)$ =	300	V
$I_C(100\%)$ =	20	A
t_f =	0,110	µs

figure 4. **IGBT**

Turn-on Switching Waveforms & definition of tr

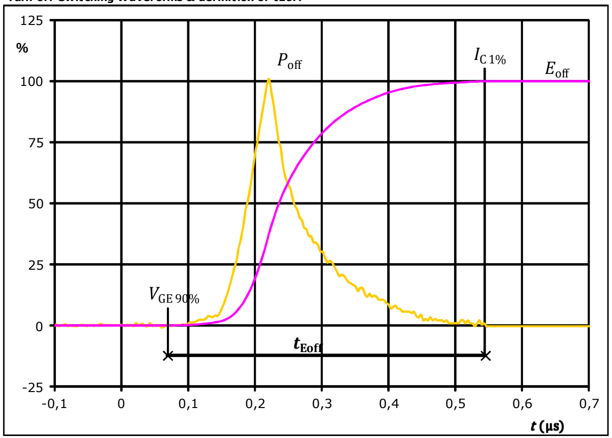


$V_C(100\%)$ =	300	V
$I_C(100\%)$ =	20	A
t_r =	0,016	µs

Inverter Switching Definitions

figure 5. **IGBT**

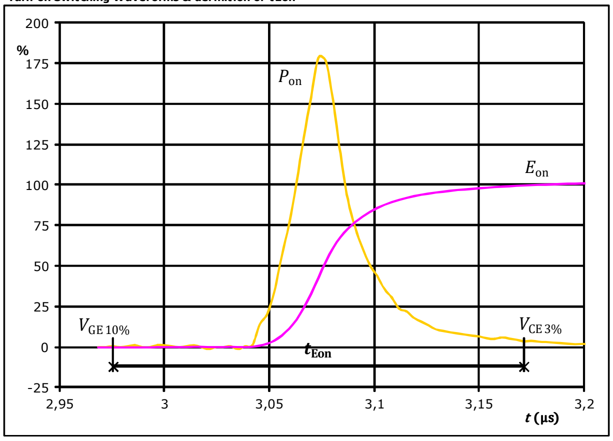
Turn-off Switching Waveforms & definition of tEoff



P_{off} (100%) =	5,98	kW
E_{off} (100%) =	0,61	mJ
t_{Eoff} =	0,48	µs

figure 6. **IGBT**

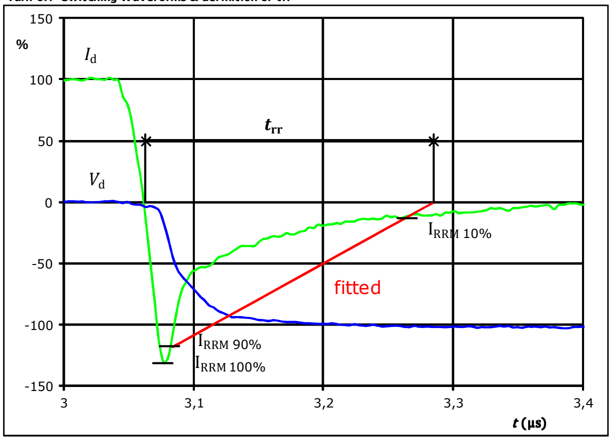
Turn-on Switching Waveforms & definition of tEon



P_{on} (100%) =	5,98	kW
E_{on} (100%) =	0,38	mJ
t_{Eon} =	0,20	µs

figure 7. **FWD**

Turn-off Switching Waveforms & definition of trr

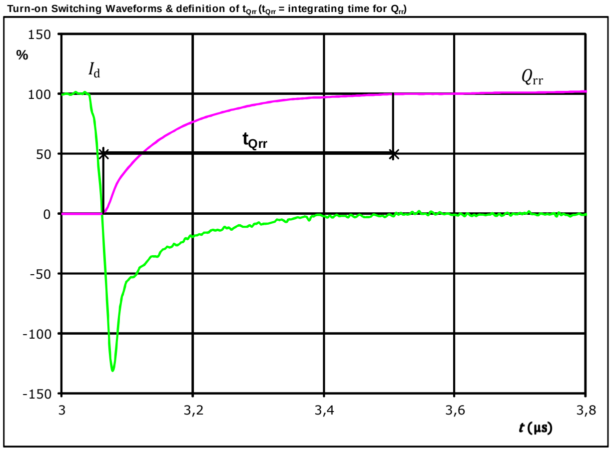


V_d (100%) =	300	V
I_d (100%) =	20	A
I_{RRM} (100%) =	-26	A
t_{rr} =	0,204	µs

Inverter Switching Definitions

figure 8. **FWD**

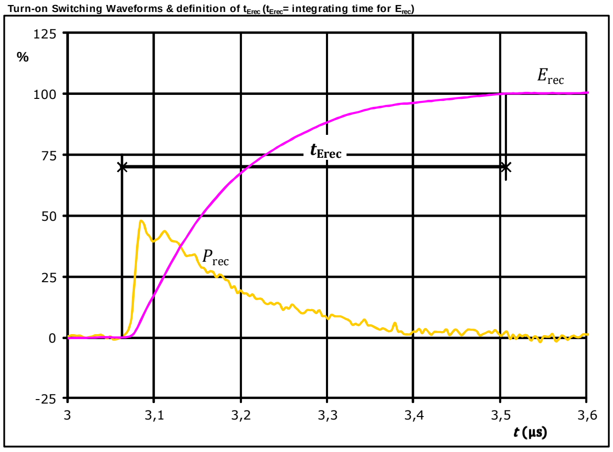
Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})



I_d (100%) =	20	A
Q_{rr} (100%) =	1,71	µC
t_{Qrr} =	0,44	µs

figure 9. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec}= integrating time for E_{rec})



P_{rec} (100%) =	5,98	kW
E_{rec} (100%) =	0,37	mJ
t_{Erec} =	0,44	µs

Ordering Code & Marking

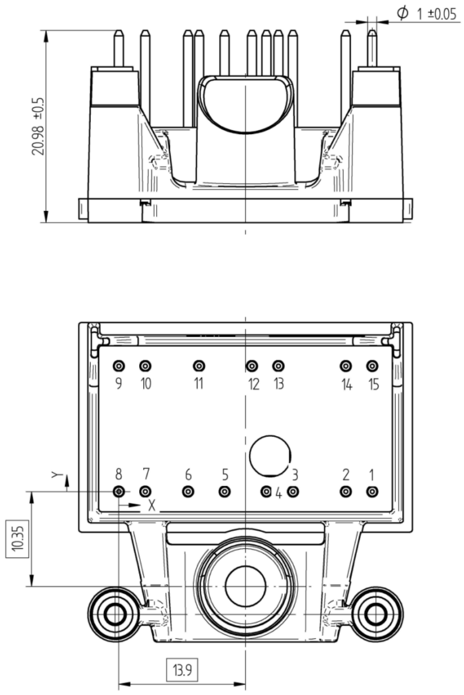
Version	Ordering Code
without thermal paste with Solder pins 17mm housing	10-0B066PA020SB-M995F09

	Name		Type&Ver	Date code	Vinco&Lot	Serial&UL
Text	NN-NNNNNNNNNNNNNN		TTTTTTTVV	WWYY	Vinco LLLLL	SSSS UL
Datamatrix	Type&Ver	Lot number	Serial	Date code		
	TTTTTTTVV	LLLLL	SSSS	WWYY		

Outline

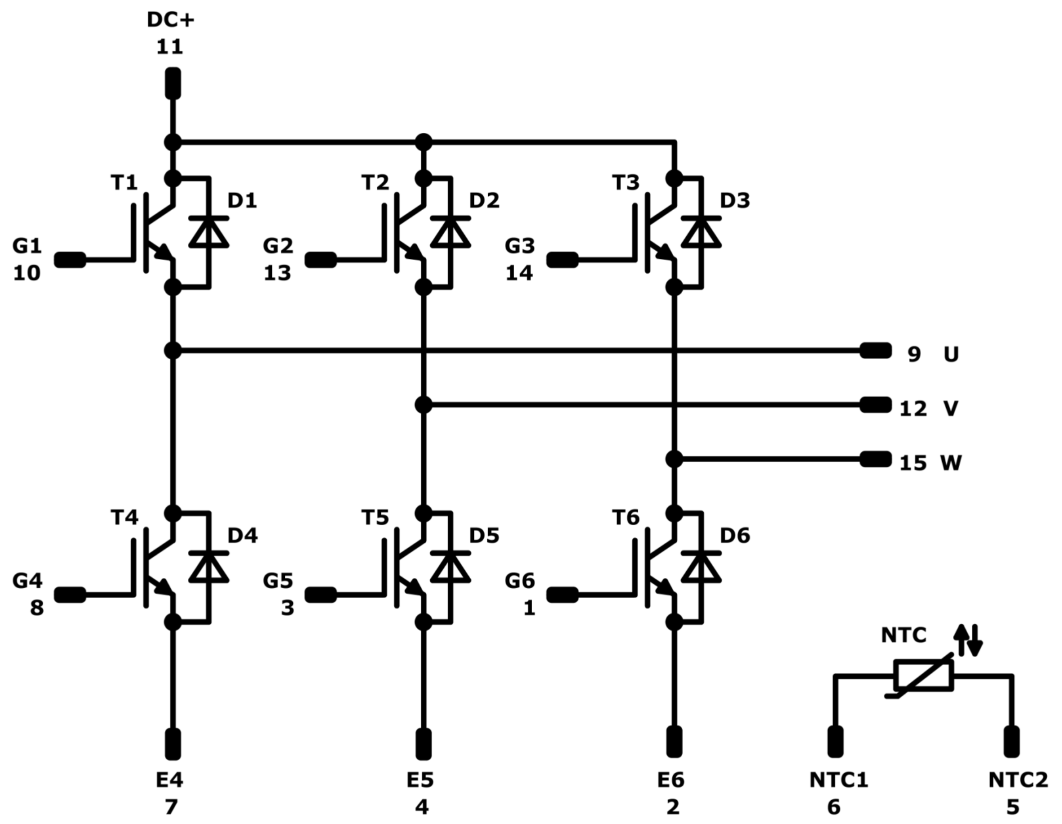
Pin table [mm]

Pin	X	Y	Function
1	27,8	0	G6
2	24,9	0	E6
3	19,1	0	G5
4	16,2	0	E5
5	11,6	0	NTC2
6	7,6	0	NTC1
7	2,9	0	E4
8	0	0	G4
9	0	13,7	U
10	2,9	13,7	G1
11	8,8	13,7	DC+
12	14,6	13,7	V
13	17,5	13,7	G2
14	24,9	13,7	G3
15	27,8	13,7	W



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance
PCB cutouts and holes see in handling instruction document

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T1-T6	IGBT	600 V	20 A	Inverter Switch	
D1-D6	FWD	600 V	20 A	Inverter Diode	
NTC	NTC			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 160	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 B packages see vincotech.com website.

Package data
Package data for *flow* 0 B packages see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-0B066PA020SB-M995F09-D3-14	23 Jun. 2017		